

RSQ045N03

Nch 30V 4.5A Power MOSFET

V_{DSS}	30V
R _{DS(on)} (Max.)	38 m Ω
I _D	4.5A
P_{D}	1.25W

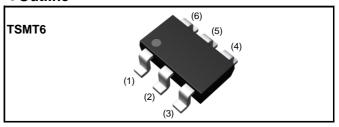
Features

- 1) Low on resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT6).
- 4) Pb-free lead plating; RoHS compliant

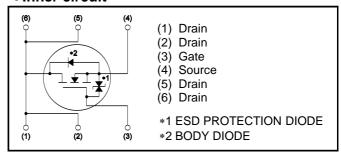
Application

DC/DC converters

Outline



●Inner circuit



Packaging specifications

	Packaging	Taping
	Reel size (mm)	180
Typo	Tape width (mm)	8
Type	Basic ordering unit (pcs)	3,000
	Taping code	TR
	Marking	QL

● Absolute maximum ratings(T_a = 25°C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	30	V
Continuous drain current	I _D ^{*1}	±4.5	А
Pulsed drain current	I _{D,pulse} *2	±18	А
Gate - Source voltage	V_{GSS}	±20	V
Power dissipation	P _D *3	1.25	W
Power dissipation	P _D *4	0.6	W
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
raiametei		Min.	Тур.	Max.	Offic
Thermal resistance, junction - ambient	R _{thJA} *3	1	-	100	°C/W
Thermal resistance, junction - ambient	R _{thJA} *4	ı	ı	208	°C/W

$\bullet \text{Electrical characteristics}(T_a = 25 ^{\circ}\text{C})$,unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit	
r ai ai nietei	Symbol	Conditions	Min.	Тур.	Max.	Offic	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	30	-	-	V	
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	I _D =1mA referenced to 25°C	-	26	-	mV/°C	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	μΑ	
Gate - Source leakage current	I_{GSS}	$V_{GS} = 20V, V_{DS} = 0V$	ı	ı	10	μΑ	
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V$, $I_D = 1mA$	1.0	ı	2.5	V	
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_{j}}$	I _D =1mA referenced to 25°C	,	-2.8	-	mV/°C	
		V _{GS} =10V, I _D =4.5A	-	27	38		
Static drain - source	D *5	V _{GS} =4.5V, I _D =4.5A	-	36	51	m O	
on - state resistance	R _{DS(on)} 5	V _{GS} =4.0V, I _D =4.5A	ı	40	56	mΩ	
		V _{GS} =10V, I _D =4.5A, T _j =125°C	ı	50	70		
Gate input resistannce	R_{G}	f = 1MHz, open drain	-	6	-	Ω	
Transconductance	g _{fs} *5	V _{DS} =10V, I _D =4.5A	3.5	7.0	-	S	

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 μ s, Duty cycle \leq 1%

^{*3} Mounted on a ceramic board (30x30x0.8mm)

^{*4} Mounted on a FR4 (15×20×0.8mm)

^{*5} Pulsed

• Electrical characteristics ($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic	
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	520	-		
Output capacitance	C _{oss}	V _{DS} = 10V	-	150	-	pF	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	95	-		
Turn - on delay time	t _{d(on)} *5	$V_{DD} \simeq 15V, V_{GS} = 10V$	-	12	-		
Rise time	t _r *5	I _D = 2.25A	-	19	-	20	
Turn - off delay time	t _{d(off)} *5	$R_L = 6.67\Omega$	-	41	-	ns	
Fall time	t _f *5	$R_G = 10\Omega$	-	14	-		

•Gate Charge characteristics($T_a = 25$ °C)

Parameter	Cumbal	Conditions	Values			Unit
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	**5	$V_{DD} \simeq 15V$, $I_D=4.5A$ $V_{GS} = 5V$	-	6.8	9.5	
Total gate charge Q _g	Qg *5	$V_{DD} = 15V, I_{D} = 4.5A$ $V_{GS} = 10V$	-	13	-	nC
Gate - Source charge	Q _{gs} *5	$V_{DD} \simeq 15V$, $I_D=4.5A$ $V_{GS} = 5V$	-	1.6	-	
Gate - Drain charge	Q _{gd} *5	$V_{GS} = 5V$	-	2.3	-	

•Body diode electrical characteristics (Source-Drain)($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai ii etei	Symbol		Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T _a = 25°C	-	-	1	А
Forward voltage	V _{SD} *5	$V_{GS} = 0V, I_{s} = 1.0A$	-	-	1.2	V

Fig.1 Power Dissipation Derating Curve

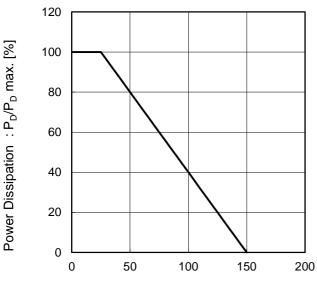
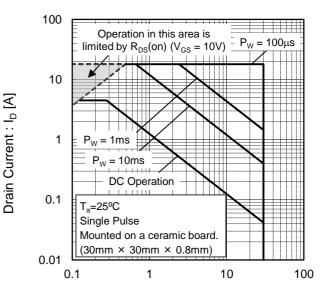


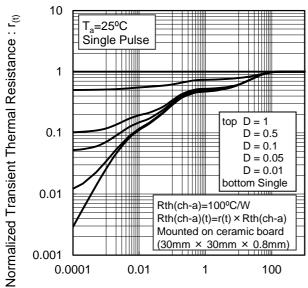
Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]

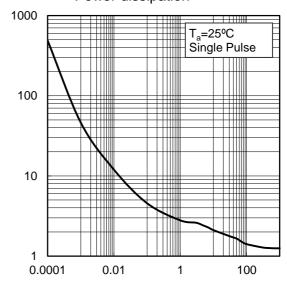
Junction Temperature : T_j [°C]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width: Pw [s]

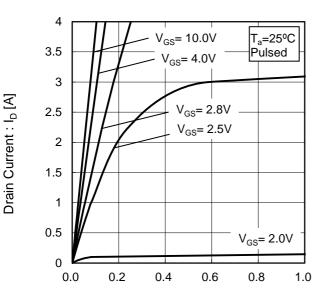
Fig.4 Single Pulse Maximum Power dissipation



Pulse Width: P_W [s]

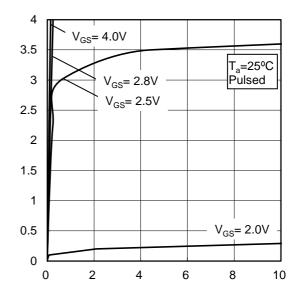
Peak Transient Power: P(W)

Fig.5 Typical Output Characteristics(I)



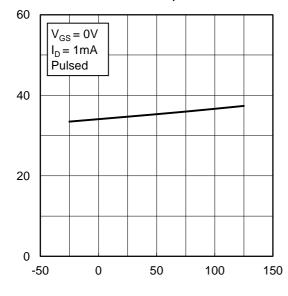
Drain - Source Voltage : V_{DS} [V]

Fig.6 Typical Output Characteristics(II)



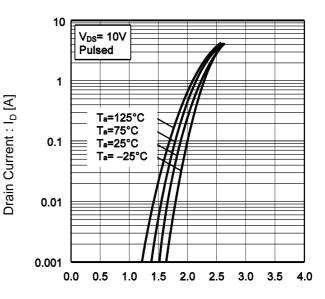
Drain - Source Voltage : V_{DS} [V]

Fig.7 Breakdown Voltage vs. Junction Temperature



Junction Temperature : T_j [°C]

Fig.8 Typical Transfer Characteristics



Gate - Source Voltage : V_{GS} [V]

Drain - Source Breakdown Voltage: V_{(BR)DSS} [V]

Drain Current : I_D [A]

Gate Threshold Voltage : $V_{GS(th)}[V]$

•Electrical characteristic curves

Fig.9 Gate Threshold Voltage

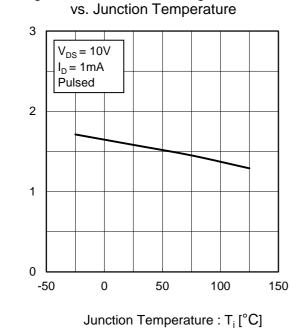


Fig.10 Transconductance vs. Drain Current

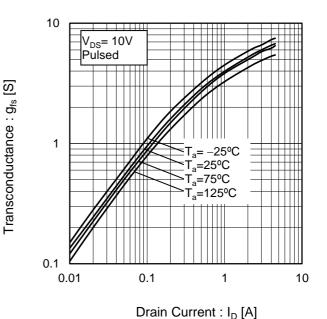


Fig.11 Drain CurrentDerating Curve

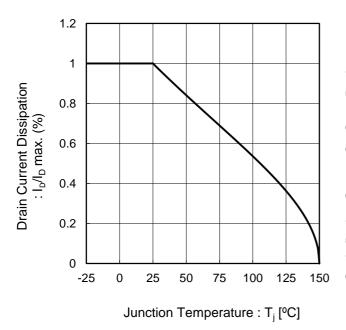
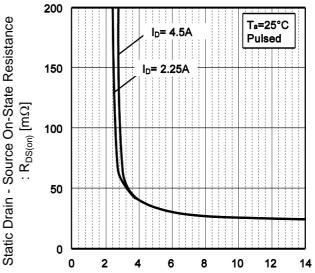


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Gate - Source Voltage : V_{GS} [V]

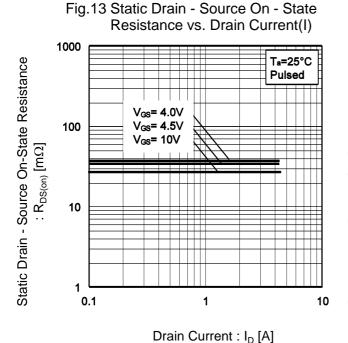


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature 60 Static Drain - Source On-State Resistance 50 40 $:R_{\text{DS(on)}}\left[\text{m}\Omega\right]$ 30 20 $V_{GS} = 10V$ $I_D = 4.5A$ Pulsed 10 0 -50 -25 0 25 50 75 100 125 150

Junction Temperature : T_i [°C]

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II) 1000 V_{GS}= 10V Static Drain - Source On-State Resistance Pulsed Ta=125°C Ta=75°C Ta=25°C 100 Ta= -25°C $: R_{\mathsf{DS}(\mathsf{on})} \ [m\Omega]$ 10 0.1 1 10 Drain Current : I_D [A]

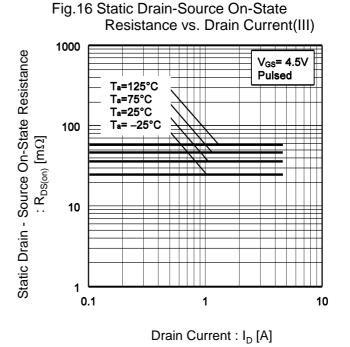


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV) 1000 Static Drain - Source On-State Resistance V_{GS}= 4.0V Pulsed Ta=125°C Ta=75°C Ta=25°C Ta= -25°C 100 $:R_{\text{DS(on)}}\left[m\Omega \right]$ 10 0.1 1 10 Drain Current : I_D [A]

Fig.18 Typical Capacitance
vs. Drain - Source Voltage

10000

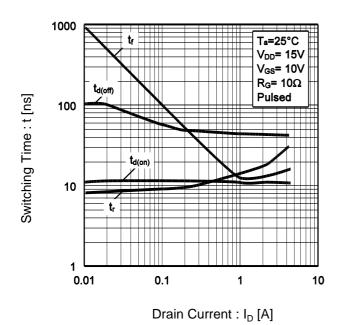
Ta=25°C
f=1MHz
Vas= 0V

Ciss

Coss

100
0.01
0.1
1
10
100

Fig.19 Switching Characteristics



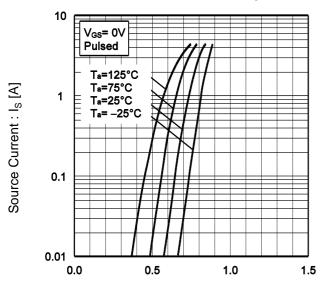
10 Ta=25°C V_{DD}= 15V $I_D = 7.5A$ $R_G = 10\Omega$ Pulsed 7 6 5 4 3 2 0 0 2 6 8 10 12 14

Fig.20 Dynamic Input Characteristics

Drain - Source Voltage : V_{DS} [V]

Gate - Source Voltage : V_{GS} [V]

Fig.21 Source Current vs. Source Drain Voltage



Source-Drain Voltage : V_{SD} [V]

●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

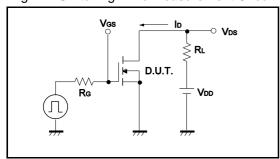


Fig.2-1 Gate Charge Measurement Circuit

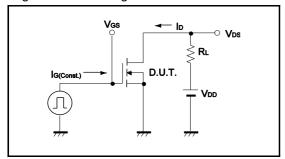


Fig.1-2 Switching Waveforms

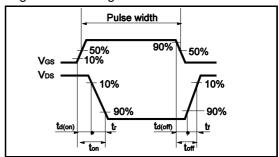
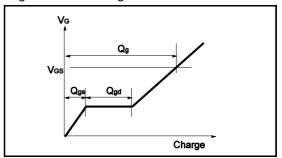
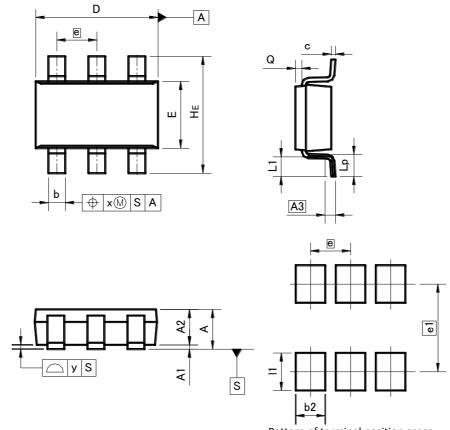


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit : mm)





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIMI	MILIMETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	-	1.00	ı	0.039
A1	0.00	0.10	0.000	0.004
A2	0.75	0.95	0.030	0.037
A3	0.3	25	0.0	10
b	0.35	0.50	0.014	0.020
С	0.10	0.26	0.004	0.010
D	2.80	3.00	0.110	0.118
Е	1.50	1.80	0.059	0.071
е	0.9	95	0.0	37
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.010
Х	_	0.20	_	0.008
у	_	0.10	_	0.004

DIM MILIMETERS			INCHES		
DIIVI	MIN	MAX	MIN	MAX	
b2		0.70	ı	0.028	
e1	2.	10	0.0	83	
l1	_	0.90	-	0.035	

Dimension in mm / inches

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